	L #	Hits	Search Text	DBs	Time Stamp
1	L1	3	"YB.sub.66"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/17 09:13
2	L2	14	"$B.sub.66"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/17 09:13
3	L3	648	(boron or B) adj rich	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/17 09:18
4	L4	4221	("427/530,455,566,250,596,597").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/17 09:20
5	L5	3938	("204/192.15-192.25,192.38").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/17 09:21

1 or 2
L8
17 hits

S/N 09/560,678

	L #	Hits	Search Text	DBs	Time Stamp
6	L6	4	(4 or 5) and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/17 09:22
7	L7	753	(4 or 5) and Boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/17 09:22

L9 (9) YB66

L6

	Document ID	Issue Date	Title	Current OR	Inventor
1	US 6281774 B1	20010828	Corrosion-resistant permanent magnet and method for producing the same	335/302	Nishiuchi, Takeshi, et al.
2	US 6054185 A	20000425	Substrate with superhard coating containing boron and nitrogen and method of making the same	427/419.7	Inspektor, Aharon
3	US 4968529 A	19901106	Process for producing a corrosion resistant permanent magnet	427/131	Hamamura, Atsushi, et al.
4	US 4837114 A	19890606	Process for producing magnets having improved corrosion resistance	427/527	Hamada, Takaki, et al.

L8

3

	Document ID	Issue Date	Title	Current OR	Inventor
1	US 6274208 B1	20010814	Liquid crystal composition and liquid crystal display device	428/1.1	Iwamatsu, Masako , et al.
2	US 6127842 A	20001003	Modified adder tree structure and method using logic and gates to gene rate carry-in values	326/38	Dalal, Parin B. , et al.
3	US 6025636 A	20000215	Surface acoustic wave device incorpora ting single crystal LiNbO.sub .3	257/416	Nakahata, Hideaki , et al.
4	US 5916634 A	19990629	Chemical vapor depositio n of W-Si-N and W-B-N	427/255.3 92	Fleming, James G. , et al.
5	US 5861630 A	19990119	Method for generatin g a boron vapor	250/423R	Becker, Richard L.

	Document ID	Issue Date	Title	Current OR	Inventor
6	US 5671154 A	19970923	Signal processing method and signal processing device for ultrasonic inspection apparatus	702/39	Iizuka, Yukinori, et al.
7	US 5621300 A	19970415	Charging control method and apparatus for power generation system	320/101	Sato, Hiroshi, et al.
8	US 5336362 A	19940809	Method for preparing yttrium 66 boride crystal for soft x-ray monochromator	117/42	Tanaka, Takaho, et al.
9	US 5187539 A	19930216	Mirror surface characteristic testing	356/124	Adachi, Iwao P., et al.
10	US 5109215 A	19920428	Means and method for monitoring a protective garment	340/540	Dennison, Everett

Citations "Prep... YB66)
"Growth... YB66)

Abst. - YB66

	Document ID	Issue Date	Title	Current OR	Inventor
11	US 5038401 A	19910806	Transmitter for remote control with operation switches having changeably displayed forms	455/92	Inotsume, Fusako
12	US 4803734 A	19890207	Method of and apparatus for detecting pattern defects	382/115	Onishi, Hiroyuki, et al.
13	US 4516851 A	19850514	Velocity measurement	356/28	Parker, John C., et al.
14	US 4012937 A	19770322	Work transfer and drive device in a transfer press	72/419	Imanishi, Shozo
15	US 3932314 A	19760113	Hexaboride electron emissive material	252/519.14	Kawabe, Ushio, et al.
16	US 3835983 A	19740917	METHOD AND APPARATUS FOR CONVEYANCE OF GOODS BY VIBRATING PLATES	198/446	Horii, Taro

(D) As appro... Table D Y/B66

	Document ID	Issue Date	Title	Current OR	Inventor
17	US 3608470 A	19710928	SYSTEM FOR AUTOMATIC CONTROL OF PROCESS OF BOILING, VACUUM COOLING AND DEHYDRATION OF FOOD STUFFS	99/330	Zabiyakin, Vyacheslav Petrovich, et al.

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	Document ID	Issue Date	Title	Current XRef	Inventor
1	US 5336362 A	19940809	Method for preparing yttrium 66 boride crystal for soft x-ray mono chromator	117/944	Tanaka, Takaho , et al.
2	JP 2001074894 A	20010323	MATERIAL FOR SPECTRAL ELEMENT THAT DISPERSES SOFT X RAYS		TANAKA, TAKAO
3	JP 60086097 A	19850515	PREPARATION OF CRYSTAL OF YB66	117/49 ; 117/937	TANAKA, TAKAO , OTANI, SHIGEKI , et al.
4	US 5336362 A	19940809	Method for preparing yttrium 66 boride crystal for soft x-ray monochromator		TANAKA, TAKAHO , KAMIMURA, YUTAKA , et al.

	Document ID	Issue Date	Title	Current XRef	Inventor
5	JP 2001074894 A	20010323	Soft X-ray part optical element material has transition elements added to yttrium boride and x-ray reflecting rate of material is increased by changing distribution and position of atoms in crystal lattice		

	Document ID	Issue Date	Title	Current XRef	Inventor
6	JP 11002698 A	19990106	Monochromator for use in spectroscopy - has several optical elements with reflecting surface fixed in revolver which is supported by holder whose rotation is controlled		
7	JP 07245409 A	19950919	Semiconductor device mfg method e.g. FRAM - involves forming semiconductor film having height resistance for oxidation over silicon substrate		

	Document ID	Issue Date	Title	Current XRef	Inventor
8	US 5336362 A	19940809	Crystalline body prepn. of 66-boride of yttrium for soft X=ray spectrograp hy - using floating melt zone method at low melt zone temp.		IN
9	JP 60086097 A	19850515	Yttrium boride crystal mfr. - using polycrystalline yttrium boride bar set in reactor for floating zone method		

DERWENT-ACC-NO: 1995-362911
DERWENT-WEEK: 199547

TITLE: Semiconductor device mfg method e.g. FRAM - involves forming
semiconductor film having height resistance for oxidation over silicon
substrate

PATENT-ASSIGNEE: MITSUBISHI ELECTRIC CORP[MITQ]

PRIORITY-DATA: 1994JP-0035794 (March 7, 1994)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
JP 07245409 A	September 19, 1995	N/A	010	H01L 029/786

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
JP07245409A	N/A	1994JP-0035794	March 7, 1994

INT-CL (IPC): H01L021/20; H01L021/8247 ; H01L027/10 ; H01L029/78 ;
H01L029/786 ; H01L029/788 ; H01L029/792

ABSTRACTED-PUB-NO: JP07245409A
BASIC-ABSTRACT: The mfg. method includes an Si substrate (11). A semiconductor
film, made of cubic SiC, BN, YB66, titanium acid, strontium, diamond and
material having high resistance for oxidation is formed outside the substrate.

A ferroelectric wiring semiconductor substrate (14) is provided over the
semiconductor film. A low resistance wiring (17) made of Cu or Ag is provided
over the semiconductor film.

ADVANTAGE - Provides high power. Obtains highly reliable semiconductor device.

CHOSEN-DRAWING: Dwg.2/11

TITLE-TERMS:
SEMICONDUCTOR DEVICE MANUFACTURE METHOD FORMING SEMICONDUCTOR FILM HEIGHT
RESISTANCE OXIDATION SILICON SUBSTRATE

ADDL-INDEXING-TERMS:
FERROELECTRIC RANDOM ACCESS MEMORY

DERWENT-CLASS: L03 U12 U14

CPI-CODES: L03-G04A; L04-C10D; L04-C10E;

EPI-CODES: U12-D02A9; U14-A03F;

SECONDARY-ACC-NO:
CPI Secondary Accession Numbers: C1995-157977
Non-CPI Secondary Accession Numbers: N1995-268909